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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Timothy Henson

Date: May 5, 2005

Serial No.: 10/603,461

Group Art Unit: 2815

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Examiner: Matthew C. Landau

Notice of Allowance Date: February 15, 2005 Confirmation No.: 3230

For: SHORT CHANNEL TRENCH MOSFET WITH REDUCED GATE CHARGE

Mail Stop: Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

COMMENTS ON EXAMINER'S AMENDMENT

Sir:

Referring to the Examiner's Amendment, it should be noted that claim 10 in the record calls for "field relief regions of said second conductivity type formed below said channel region". This limitation, however does not appear in the recitation of claim 10 as set forth in the Examiner's Amendment. Please note that the last limitation in claim 10 should read as follows:

a source contact formed over said epitaxial layer and in ohmic contact with said plurality of source regions; and field relief regions of said second conductivity type formed below said channel region, wherein a conductivity of said first regions of said first conductivity type and a conductivity of said field relief regions [being selected to create a superjunction in said device] are substantially equal.

This limitation is consistent with the record, and includes the amendments agreed to previously.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on May 5, 2005

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Respectfully submitted,

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